

VERSION SHOWING THE AMENDMENTS TO THE CLAIMS

Amend the claims as follows:

1. (Currently amended). An organic logic gate comprising:

a circuit having an output and comprising at least one organic charging field effect transistor (charging FET) on a substrate, the charging FET including a first structured layer comprising source and drain having source, drain and gate electrodes, followed by a semiconductor layer on the electrodes followed by a layer of insulating material on the semiconductor layer and adjacent to and contiguous with a second electrode layer and at least one switching organic field effect transistor (switching FET) having at least one gate electrode, a source electrode and a drain electrode, the drain-source electrodes of the charging and switching transistors being arranged to be coupled in series between a voltage source and a reference potential such that the gate electrode of the charging FET is not connected via an electrical line directly to the voltage source, to the reference potential, to the input or to the output, wherein the gate electrode of the charging FET is directly capacitively coupled to one of the source/drain electrodes of the charging FET.

Claim 2, canceled.

3. (Currently amended). The organic logic gate as claimed in Claim [[2]] 1 wherein the capacitive coupling is achieved by the gate electrode of the charging FET overlapping the one source/drain electrode of the charging FET.

Claims 4-7, canceled.

8. (Previously presented) The organic logic gate as claimed in Claim 1 wherein the organic logic gate is constructed without plated-through holes.

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